

Silicon N-Channel MOS FET



November 1996

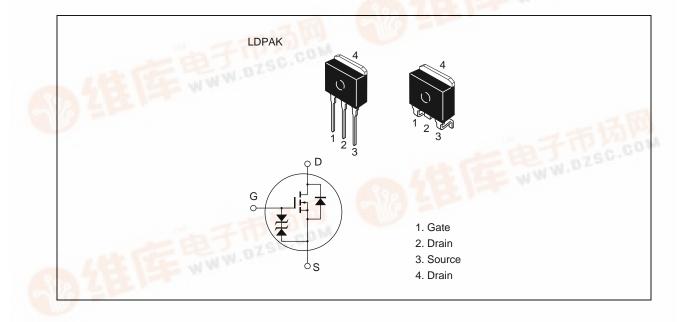
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline





Absolute Maximum Ratings (Ta = 25° C)

Item	Symbol	Ratings	Unit	
Drain to source voltage	V _{DSS}	900	V	
Gate to source voltage	V _{GSS}	±30	V	
Drain current	I _D	4	А	
Drain peak current	↓ D(pulse)	10	А	
Body to drain diode reverse drain current	I _{DR}	4	A	
Channel dissipation	Pch* ²	60	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at $T_c = 25^{\circ}C$

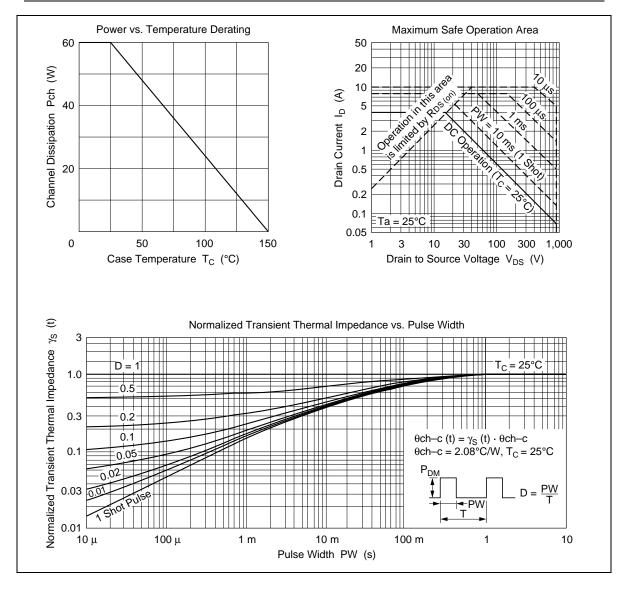
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Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{\scriptscriptstyle (BR)DSS}$	900	_	_	V	$I_{D} = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{\scriptscriptstyle (BR)GSS}$	±30	_	_	V	$I_{_{\rm G}} = \pm 100 \ \mu A, \ V_{_{\rm DS}} = 0$
Gate to source leak current	I _{GSS}	—		±10	μA	$V_{_{GS}} = \pm 25 \text{ V}, V_{_{DS}} = 0$
Zero gate voltage drain current	I _{DSS}	_		250	μA	$V_{\rm DS} = 720 \text{ V}, \text{ V}_{\rm GS} = 0$
Gate to source cutoff voltage	$V_{\rm GS(off)}$	2.0	—	3.0	V	$I_{_{D}} = 1 \text{ mA}, V_{_{DS}} = 10 \text{ V}$
Static Drain to source on state resistance	$R_{\scriptscriptstyle DS(\text{on})}$	_	3.0	4.0	Ω	$I_{D} = 2 \text{ A}, \text{ V}_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	yfs	1.7	2.7	—	S	$I_{D} = 2 \text{ A}, \text{ V}_{DS} = 20 \text{ V}^{*1}$
Input capacitance	Ciss	_	740	_	pF	$V_{_{DS}} = 10 \text{ V}, V_{_{GS}} = 0,$
Output capacitance	Coss	—	305	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	—	150	_	pF	
Turn-on delay time	t _{d(on)}	_	15	_	ns	$I_{_{D}} = 2 \text{ A}, \text{ V}_{_{GS}} = 10 \text{ V},$
Rise time	t _r	—	60	—	ns	R _L = 15 Ω
Turn-off delay time	$t_{d(off)}$	—	100	—	ns	
Fall time	t _f	—	80	—	ns	
Body to drain diode forward voltage	V_{DF}	_	0.9	_	V	$I_{F} = 4 A, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}	—	800	—	ns	$I_{F} = 4 \text{ A}, V_{GS} = 0,$ $di_{F}/dt = 100 \text{ A}/\mu\text{s}$
Nata A Dulas test						

Note 1. Pulse test

See characteristic curves of 2SK1340.



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